INTEGRATED CIRCUITS, SILICON MONOLITHIC, BIPOLAR, ADVANCED LOW POWER SCHOTTKY,

DUAL, 4-LINE-TO-1-LINE DATA

SELECTOR/MULTIPLEXER WITH

3-STATE OUTPUTS,

BASED ON TYPE 54ALS253

ESCC Detail Specification No. 9408/031

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INTEGRATED CIRCUITS, SILICON MONOLITHIC, BIPOLAR, ADVANCED LOW POWER SCHOTTKY, DUAL, 4-LINE-TO-1-LINE DATA SELECTOR/MULTIPLEXER WITH 3-STATE OUTPUTS, BASED ON TYPE 54ALS253

ESA/SCC Detail Specification No. 9408/031

space components
coordination group

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Issue 2	February 1992		
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DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	CHANGE		Approved DCR No.
		Reference	Item	
		This Issue supersedes Issue 1 and incorporates all modifications defined in Revisions 'A' and 'B' to Issue 1 and the following DCR's:-		
		Cover Page		None
		DCN		None
		Table 1(a)	: Lead Material and/or Finish amended	22881
		Figures 2	: Imperial dimensions and references deleted	22881
		Figure 2(c)	: In drawing, Note 6 corrected to "10"	23456
		Notes to Figures	: Title amended	22881
			: Note 1, amended to read "...Figure 2(b)"	22821
		Figure 3(a)	: Comparison Table added	22881
		Figure 3(b)	: Note 1 amended	23456
		Para. 4.2.2	: Deviation deleted, "None." added	21048
		Para. 4.2.4	: Deviation deleted, "None." added	22919
		Para. 4.2.5	: Deviation deleted, "None." added	22919
		Para. 4.4.2	: Paragraph amended	22881
		Para. 4.5.2	: Amended to read "...Figure 2(b)"	22881
		Para. 4.5.3	: "Type Variant, as applicable" amended to refer to Table 1(a)	23455
		Para. 4.6.3	: Reference to functional test sequence deleted	23455
		Para. 4.7.1	: Expanded to identify the stated temperature as T_{amb}	23455
		Figures 4(a), (c)	: Figures corrected	23456
		Para. 4.8	: Title expanded	23455
'A'	June '94	P1. Cover Page		None
		P2. DCN		None
		P15. Para. 4.3.2	: Weights amended	221047

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TABLES

FIGURES

APPENDICES (Applicable to specific Manufacturers only)

1. **GENERAL**

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, bipolar, advanced low power Schottky, Dual, 4-Line-to-1-Line Data Selector/Multiplexer with 3-State Outputs, based on Type 54ALS253. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 TRUTH TABLE

As per Figure 3(b).

1.8 CIRCUIT SCHEMATIC

As per Figure 3(c).

1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).

TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	D7
02	FLAT	2(a)	G4
03	CCP	2(b)	7
04	CCP	2(b)	4
05	DIL	2(c)	D7
06	DIL	2(c)	G4

TABLE 1(b) - MAXIMUM RATINGS

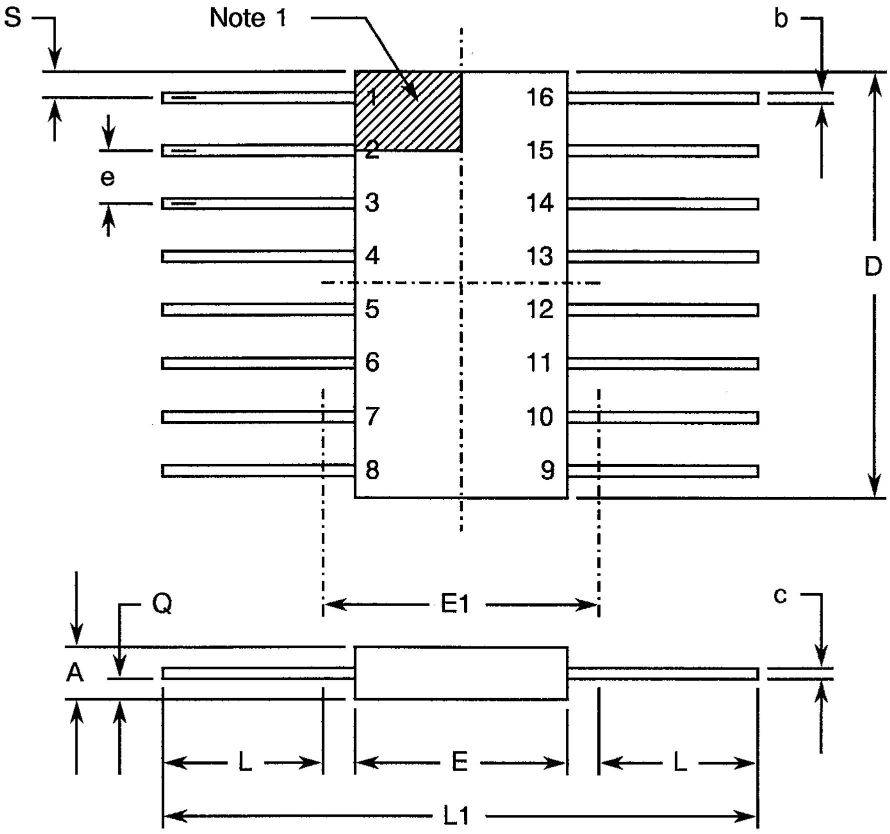
NO.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Supply Voltage	V_{CC}	−0.5 to 7.0	V	-
2	Input Voltage	V_{IN}	−0.5 to 7.0	V	Note 1
2	Voltage Applied to Disabled 3-State Output	V_Z	5.5	V	-
4	Device Dissipation	P_D	77	mWdc	Note 2
5	Operating Temperature Range	T_{op}	−55 to +125	°C	-
6	Storage Temperature Range	T_{stg}	−65 to +150	°C	-
7	Soldering Temperature For FP and DIP For CCP	T_{sol}	 +265 +245	°C	 Note 3 Note 4

NOTES

1. Input Current limited to −18mA.
2. Must withstand added P_D due to short circuit conditions (i.e. I_{OS}) at 1 output for 5 seconds.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the package and the same lead shall not be resoldered until 3 minutes have elapsed.
4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - FLAT PACKAGE

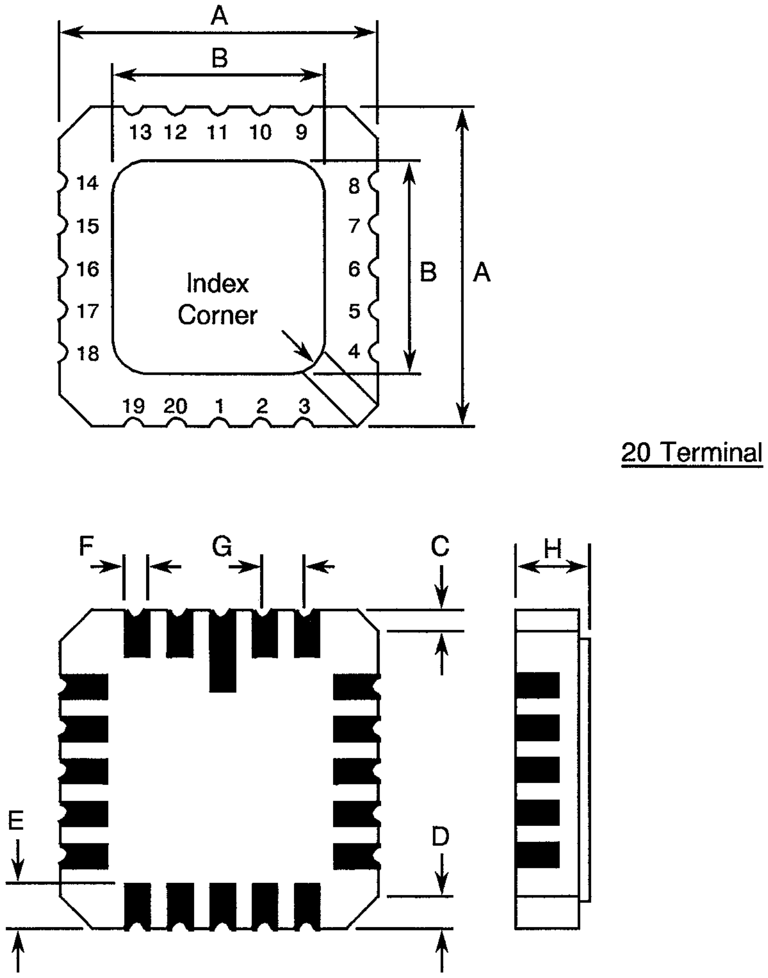


SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	1.24	2.03	
b	0.38	0.48	8
c	0.08	0.15	8
D	9.65	11.02	
E	6.10	6.60	
E1	-	7.11	4
e	1.27 TYPICAL		5, 9
L	6.35	9.40	
L1	19.05	-	
Q	0.25	0.89	2
S	0.25	0.76	7

NOTES: See Page 10.

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - SQUARE CHIP CARRIER PACKAGE (3 LAYER BASE)

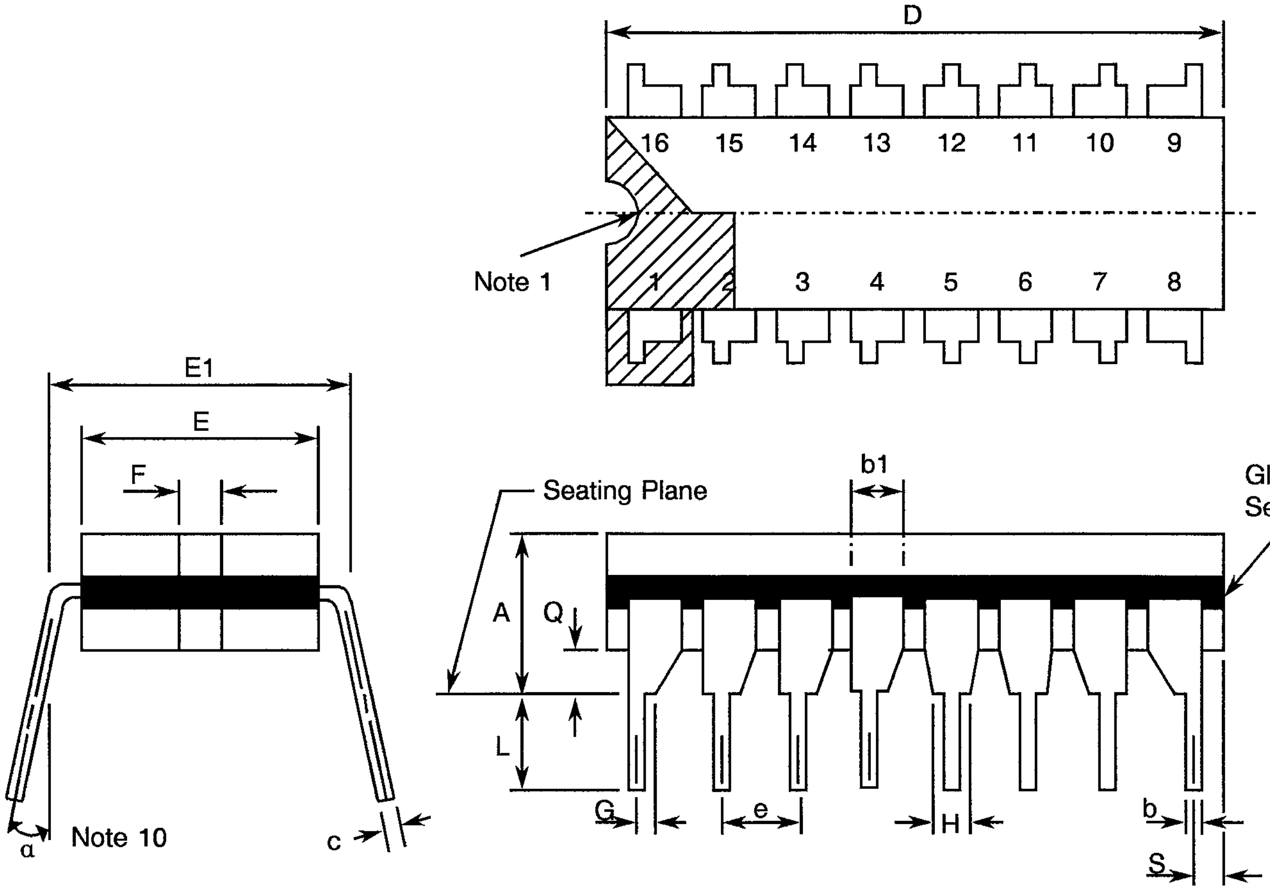


SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	8.687	9.093	
B	7.798	9.093	
C	0.250	0.510	11
D	0.889	1.143	12
E	1.140	1.400	8
F	0.559	0.712	8
G	1.27 TYPICAL		5, 9
H	1.630	2.540	

NOTES: See Page 10.

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(c) - DUAL-IN-LINE PACKAGE



SYMBOL	MILLIMETRES		NOTES
	MIN	MAX	
A	-	5.08	
b	0.38	0.58	8
b1	-	1.78	8
c	0.203	0.356	8
D	19.18	19.94	
E	6.22	7.11	
E1	7.37	7.87	4
e	2.54 TYPICAL		6, 9
G	0.305	-	13
H	0.76	-	14
L	3.30	5.08	
Q	0.51	2.03	3
S	0.38	1.27	7
α	0°	15°	10

NOTES: See Page 10.

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

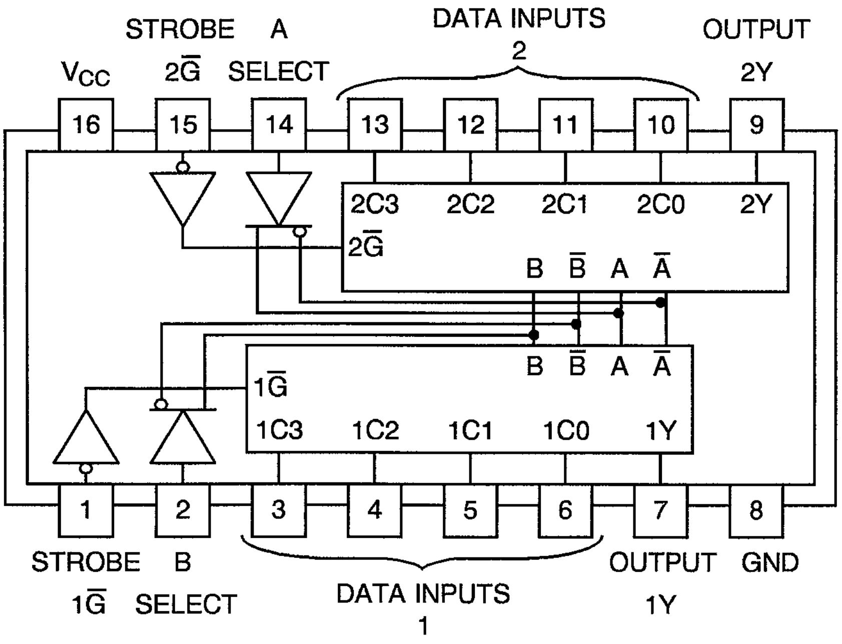
NOTES TO FIGURES 2(a) TO 2(c) INCLUSIVE

1. Index area; a notch or dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages the index shall be as defined in Figure 2(b).
2. Dimension Q shall be measured at the point of exit of the lead from the body.
3. Dimension Q shall be measured from the seating plane to the base plane.
4. This dimension allows for off-centre lids, meniscus and glass overrun.
5. The true position pin or terminal spacing is 1.27mm between centrelines. Each pin or terminal centreline shall be located within ±0.13mm of its true longitudinal position relative to Pins 1 and the highest pin number.
6. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ±0.25mm of its true longitudinal position relative to Pins 1 and the highest pin number.
7. Applies to all 4 corners.
8. All leads or terminals.
9. 14 spaces for flat and dual-in-line packages.

   16 spaces for chip carrier packages.
10. Lead centre when α is 0°.
11. Index corner only - 2 dimensions.
12. 3 non-index corners - 6 dimensions.
13. 4 Terminals.
14. 12 Terminals.

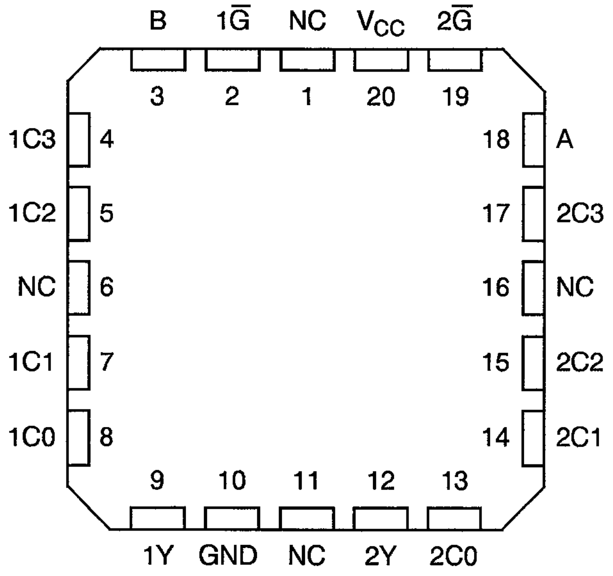
FIGURE 3(a) - PIN ASSIGNMENT

DUAL-IN-LINE AND FLAT PACKAGE



TOP VIEW

CHIP CARRIER PACKAGE



TOP VIEW

FLAT PACKAGE AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

FLAT PACKAGE AND DUAL-IN-LINE PIN OUTS	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
CHIP CARRIER PIN OUTS	2	3	4	5	7	8	9	10	12	13	14	15	17	18	19	20

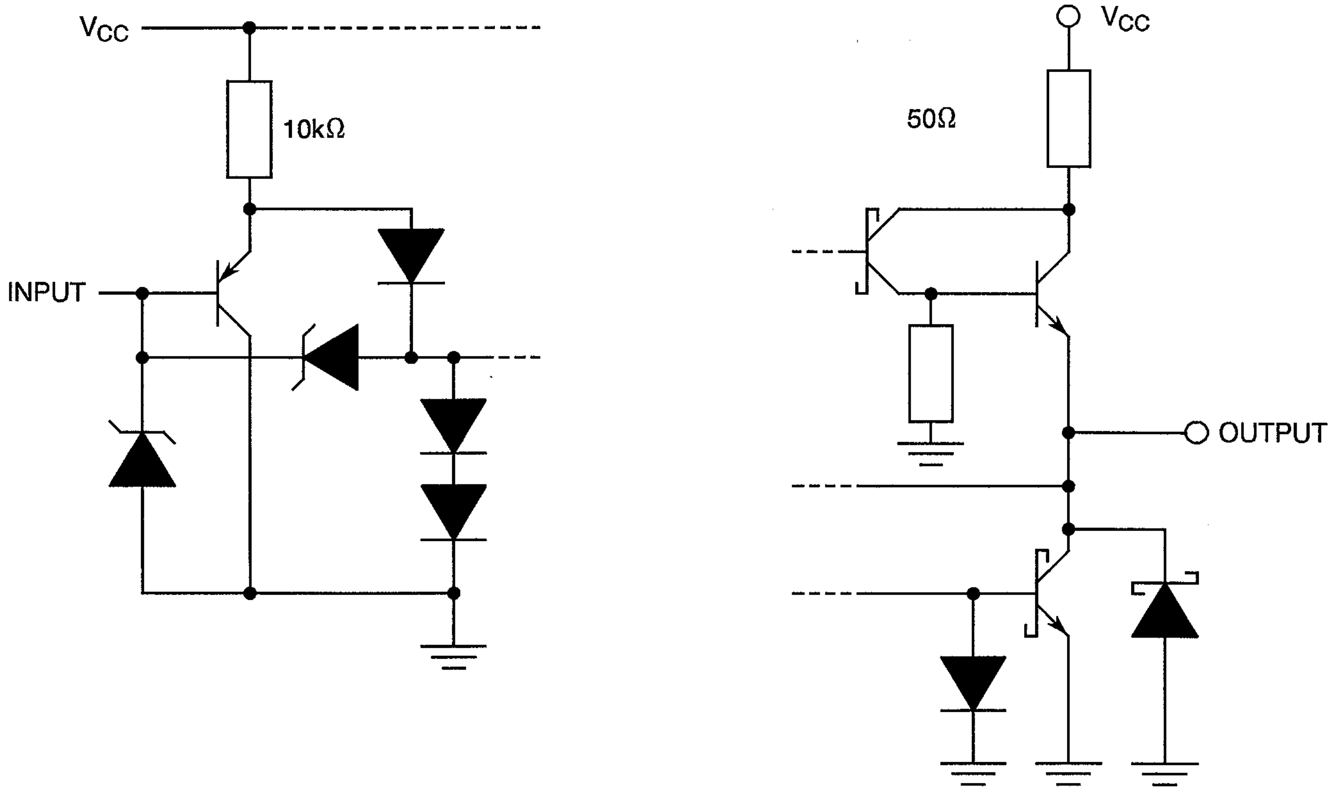
FIGURE 3(b) - TRUTH TABLE

SELECT INPUTS		DATA INPUTS				STROBE	OUTPUT
B	A	C0	C1	C2	C3	$\overline{G}$	Y
X	X	X	X	X	X	H	Z
L	L	L	X	X	X	L	L
L	L	H	X	X	X	L	H
L	H	X	L	X	X	L	L
L	H	X	H	X	X	L	H
H	L	X	X	L	X	L	L
H	L	X	X	H	X	L	H
H	H	X	X	X	L	L	L
H	H	X	X	X	H	L	H

NOTES

1. Logic Level Definitions: L = Low Level, H = High Level, Z = High Impedance, X = Irrelevant.
2. Address Inputs A and B are common to both sections.

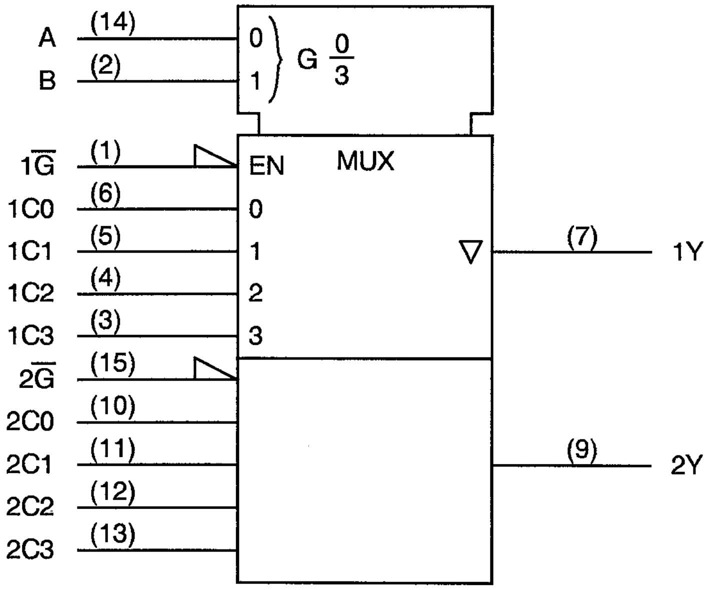
FIGURE 3(c) - CIRCUIT SCHEMATIC



EQUIVALENT OF EACH INPUT

TYPICAL OF OUTPUTS

FIGURE 3(d) - FUNCTIONAL DIAGRAM



NOTES

1. Pin numbers shown are for flat and dual-in-line packages; for chip carrier pins, see Figure 3(a).

2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

(a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.

(b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:-

$I_{OS/2}$ - One half of the true output short circuit current.
I_{OZH} - Off state, output current high.
I_{OZL} - Off state, output current low.
I_{CCZ} - Supply current, outputs disabled.

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Controls

None.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in Tests (Chart III)

(a) Para. 7.1.1(a), "High Temperature Reverse Bias" tests and subsequent electrical measurements related to this test shall be omitted.

(b) Para. 9.9.2, "Electrical Measurements at High and Low Temperatures": Only a test result summary, based on go-no-go tests and presented in histogram form is required.

4.2.4 Deviations from Qualification Tests (Chart IV)

None.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 0.7 grammes for the flat package, 0.6 grammes for the chip carrier package and 2.2 grammes for the dual-in-line package.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

For dual-in-line and flat packages, the material shall be either Type 'D' or Type 'G' with either Type '4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. For chip carrier packages, the finish shall be either Type '4' or Type '7' in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

(a) Lead Identification.

(b) The SCC Component Number.

(c) Traceability Information.

4.5.2 Lead Identification

For dual-in-line and flat packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(b).

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

940803102B

Detail Specification Number

Type Variant (see Table 1(a))

Testing Level (B or C, as applicable)

4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at $T_{amb} = +125(+0-5)$ °C and $-55(+5-0)$ °C respectively.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Power Burn-in

Circuits for use in performing the power burn-in tests are shown in Figure 5 of this specification.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 13	Input Current High Level 1	I_{IH1}	3010	4(a)	$V_{CC} = 5.5V$, $V_{IN} = 2.7V$ (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	20	μA
14 to 25	Input Current High Level 2 (Max. Input Voltage)	I_{IH2}	3010	4(a)	$V_{CC} = 5.5V$, $V_{IN} = 7.0V$ (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	100	μA
26 to 37	Input Clamp Voltage	V_{IC}	3008	4(b)	$V_{CC} = 4.5V$, $I_{IN} = -18mA$ Note 2 (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	-1.5	V
38 to 49	Input Current Low Level	I_{IL}	3009	4(c)	$V_{CC} = 5.5V$, $V_{IL} = 0.4V$ (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	-100	μA
50 to 51	Output Voltage Low Level	V_{OL}	3007	4(d)	$V_{CC} = 4.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OL} = 12mA$ (Pins D/F 7-9) (Pins C 9-12)	-	0.4	V
52 to 53	Output Voltage High Level 1	V_{OH1}	3006	4(e)	$V_{CC} = 4.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OH} = -1.0mA$ (Pins D/F 7-9) (Pins C 9-12)	2.4	-	V
54 to 55	Output Voltage High Level 2	V_{OH2}	3006	4(e)	$V_{CC} = 4.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OH} = -0.4mA$ (Pins D/F 7-9) (Pins C 9-12)	2.5	-	V
56 to 57	Output Voltage High Level 3	V_{OH3}	3006	4(e)	$V_{CC} = 5.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OH} = -0.4mA$ (Pins D/F 7-9) (Pins C 9-12)	3.5	-	V

NOTES: See Page 20.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
58 to 59	One Half of the True Output Short Circuit Current	$I_{OS/2}$	3011	4(f)	$V_{CC} = 5.5V$, $V_{OUT} = 2.25V$ Note 3 (Pins D/F 7-9) (Pins C 9-12)	−30	−112	mA
60 to 61	Off State Output Current High Level Applied	I_{OZH}	-	4(g)	$V_{CC} = 5.5V$, $V_{OUT} = 2.7V$ (Pins D/F 7-9) (Pins C 9-12)	-	20	µA
62 to 63	Off State Output Current Low Level Applied	I_{OZL}	-	4(g)	$V_{CC} = 5.5V$, $V_{OUT} = 0.4V$ (Pins D/F 7-9) (Pins C 9-12)	-	−20	µA
64	Supply Current Outputs Enabled	I_{CC}	3005	4(h)	$V_{CC} = 5.5V$ Note 4 (Pin D/F 16) (Pin C 20)	-	12	mA
65	Supply Current Outputs Disabled	I_{CCZ}	3005	4(h)	$V_{CC} = 5.5V$ Note 4 (Pin D/F 16) (Pin C 20)	-	14	mA

NOTES: See Page 20.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP) (NOTE 5)	LIMITS		UNIT
						MIN	MAX	
66 to 73	Propagation Delay Low to High from A to B to Y	t_{PLH}	3003	4(i)	V_{CC} = 4.5 and 5.5V C_L = 50pF $R_1 = R_2 = 500\Omega$ Pins D/F — Pins C 2 to 7 — 3 to 9 2 to 9 — 3 to 12 14 to 7 — 18 to 9 14 to 9 — 18 to 12	5.0	25	ns
74 to 81	Propagation Delay High to Low from A to B to Y	t_{PHL}	3003	4(i)	V_{CC} = 4.5 and 5.5V C_L = 50pF $R_1 = R_2 = 500\Omega$ Pins D/F — Pins C 2 to 7 — 3 to 9 2 to 9 — 3 to 12 14 to 7 — 18 to 9 14 to 9 — 18 to 12	5.0	25	ns
82 to 97	Propagation Delay Low to High from any C to Y	t_{PLH}	3003	4(i)	V_{CC} = 4.5 and 5.5V C_L = 50pF $R_1 = R_2 = 500\Omega$ Pins D/F — Pins C 3 to 7 — 4 to 9 4 to 7 — 5 to 9 5 to 7 — 7 to 9 6 to 7 — 8 to 9 10 to 9 — 13 to 12 11 to 9 — 14 to 12 12 to 9 — 15 to 12 13 to 9 — 17 to 12	2.0	12	ns
98 to 113	Propagation Delay High to Low from any C to Y	t_{PHL}	3003	4(i)	V_{CC} = 4.5 and 5.5V C_L = 50pF $R_1 = R_2 = 500\Omega$ Pins D/F — Pins C 3 to 7 — 4 to 9 4 to 7 — 5 to 9 5 to 7 — 7 to 9 6 to 7 — 8 to 9 10 to 9 — 13 to 12 11 to 9 — 14 to 12 12 to 9 — 15 to 12 13 to 9 — 17 to 12	3.0	17	ns

NOTES: See Page 20.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP (NOTE 5)	LIMITS		UNIT
						MIN	MAX	
114 to 117	Output Enable Time to High Level from $\overline{G}$ to Y	t_{PZH}	3003	4(i)	$V_{CC} = 4.5$ and 5.5V $C_L = 50pF$ $R_1 = R_2 = 500\Omega$ Pins D/F Pins C 1 to 7 2 to 9 15 to 9 19 to 12	3.0	17	ns
118 to 121	Output Enable Time to Low Level from $\overline{G}$ to Y	t_{PZL}	3003	4(i)	$V_{CC} = 4.5$ and 5.5V $C_L = 50pF$ $R_1 = R_2 = 500\Omega$ Pins D/F Pins C 1 to 7 2 to 9 15 to 9 19 to 12	4.0	19	ns
122 to 125	Output Disable Time to High Level from $\overline{G}$ to Y	t_{PHZ}	3003	4(i)	$V_{CC} = 4.5$ and 5.5V $C_L = 50pF$ $R_1 = R_2 = 500\Omega$ Pins D/F Pins C 1 to 7 2 to 9 15 to 9 19 to 12	2.0	12	ns
126 to 129	Output Disable Time to Low Level from $\overline{G}$ to Y	t_{PLZ}	3003	4(i)	$V_{CC} = 4.5$ and 5.5V $C_L = 50pF$ $R_1 = R_2 = 500\Omega$ Pins D/F Pins C 1 to 7 2 to 9 15 to 9 19 to 12	2.0	16	ns

NOTES

1. Go-no-go test with $V_{IL} = 0.3V$, $V_{IH} = 3.0V$, trip point 1.5V.
2. All inputs and outputs not under test shall be open.
3. No more than 1 output should be tested at a time.
4. For I_{CC} : $1\overline{G}$ Grounded, $2\overline{G}$ Grounded.
   For I_{CCZ} : $1\overline{G}$ at 4.5V, $2\overline{G}$ at 4.5V.
5. Propagation delay measurements shall be performed as a go-no-go test on a 100% basis. Read-and-record measurements shall be performed on an LTPD7 sample basis following the Chart III Burn-in Test.

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, +125(+0−5) °C AND −55(+5−0) °C

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 13	Input Current High Level 1	I_{IH1}	3010	4(a)	$V_{CC} = 5.5V$, $V_{IN} = 2.7V$ (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	20	µA
14 to 25	Input Current High Level 2 (Max. Input Voltage)	I_{IH2}	3010	4(a)	$V_{CC} = 5.5V$, $V_{IN} = 7.0V$ (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	100	µA
26 to 37	Input Clamp Voltage	V_{IC}	3008	4(b)	$V_{CC} = 4.5V$, $I_{IN} = -18mA$ Note 2 (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	−1.5	V
38 to 49	Input Current Low Level	I_{IL}	3009	4(c)	$V_{CC} = 5.5V$, $V_{IL} = 0.4V$ (Pins D/F 1-2-3-4-5-6-10-11-12-13-14-15) (Pins C 2-3-4-5-7-8-13-14-15-17-18-19)	-	−100	µA
50 to 51	Output Voltage Low Level	V_{OL}	3007	4(d)	$V_{CC} = 4.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OL} = 12mA$ (Pins D/F 7-9) (Pins C 9-12)	-	0.4	V
52 to 53	Output Voltage High Level 1	V_{OH1}	3006	4(e)	$V_{CC} = 4.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OH} = -1.0mA$ (Pins D/F 7-9) (Pins C 9-12)	2.4	-	V
54 to 55	Output Voltage High Level 2	V_{OH2}	3006	4(e)	$V_{CC} = 4.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OH} = -0.4mA$ (Pins D/F 7-9) (Pins C 9-12)	2.5	-	V
56 to 57	Output Voltage High Level 3	V_{OH3}	3006	4(e)	$V_{CC} = 5.5V$, $V_{IH} = 2.0V$ $V_{IL} = 0.7V$, $I_{OH} = -0.4mA$ (Pins D/F 7-9) (Pins C 9-12)	3.5	-	V

NOTES: See Page 20.

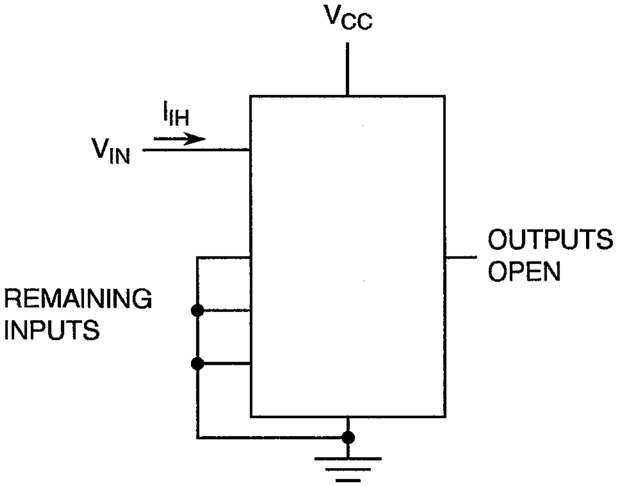
TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, +125(+0−5) °C AND −55(+5−0) °C (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD 883	TEST FIG.	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP C = CCP)	LIMITS		UNIT
						MIN	MAX	
58 to 59	One Half of the True Output Short Circuit Current	$I_{OS/2}$	3011	4(f)	$V_{CC} = 5.5V$, $V_{OUT} = 2.25V$ Note 3 (Pins D/F 7-9) (Pins C 9-12)	−30	−112	mA
60 to 61	Off State Output Current High Level Applied	I_{OZH}	-	4(g)	$V_{CC} = 5.5V$, $V_{OUT} = 2.7V$ (Pins D/F 7-9) (Pins C 9-12)	-	20	µA
62 to 63	Off State Output Current Low Level Applied	I_{OZL}	-	4(g)	$V_{CC} = 5.5V$, $V_{OUT} = 0.4V$ (Pins D/F 7-9) (Pins C 9-12)	-	−20	µA
64	Supply Current Outputs Enabled	I_{CC}	3005	4(h)	$V_{CC} = 5.5V$ Note 4 (Pin D/F 16) (Pin C 20)	-	12	mA
65	Supply Current Outputs Disabled	I_{CCZ}	3005	4(h)	$V_{CC} = 5.5V$ Note 4 (Pin D/F 16) (Pin C 20)	-	14	mA

NOTES: See Page 20.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

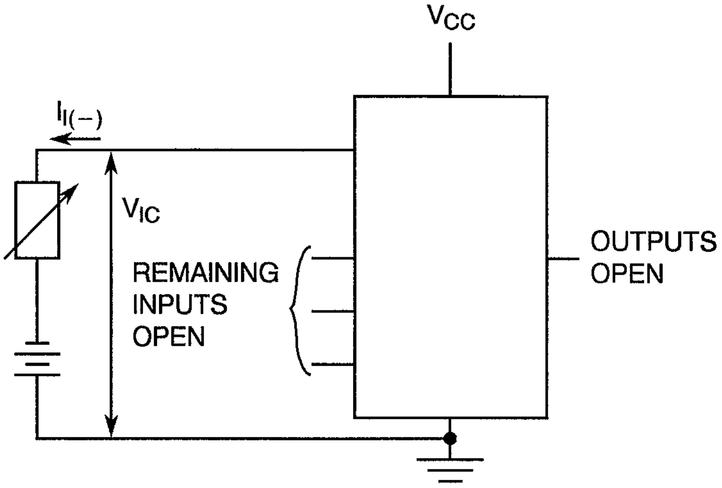
FIGURE 4(a) - INPUT CURRENT HIGH LEVEL



NOTES

1. Each input to be tested separately.

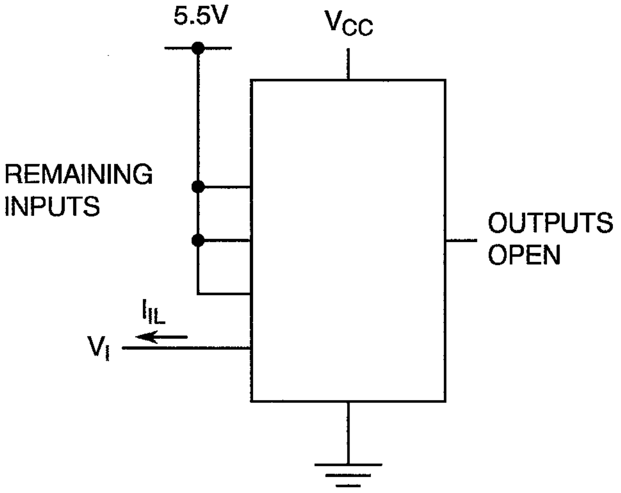
FIGURE 4(b) - INPUT CLAMP VOLTAGE



NOTES

1. Each input to be tested separately.

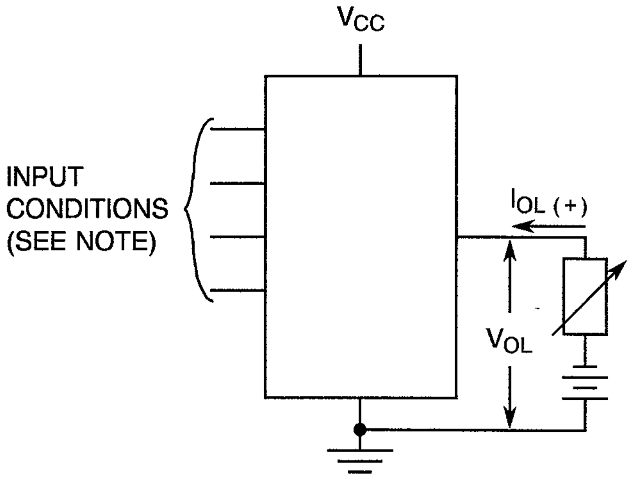
FIGURE 4(c) - LOW LEVEL INPUT CURRENT



NOTES

1. Each input to be tested separately.

FIGURE 4(d) - LOW LEVEL OUTPUT VOLTAGE

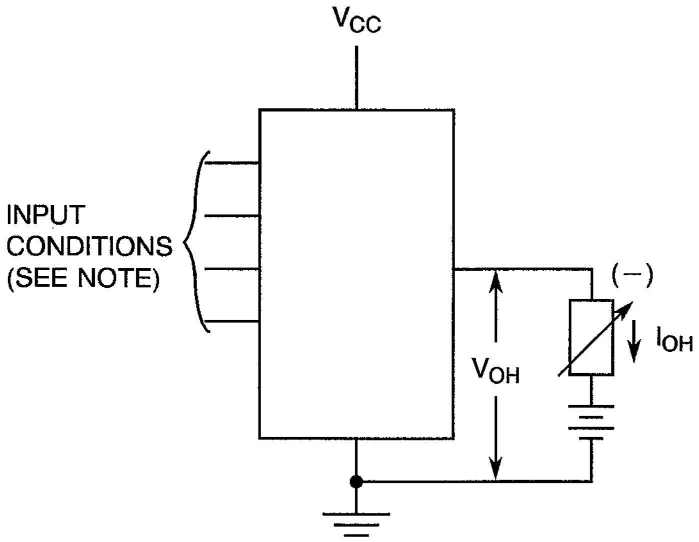


NOTES

1. Test per Truth Table

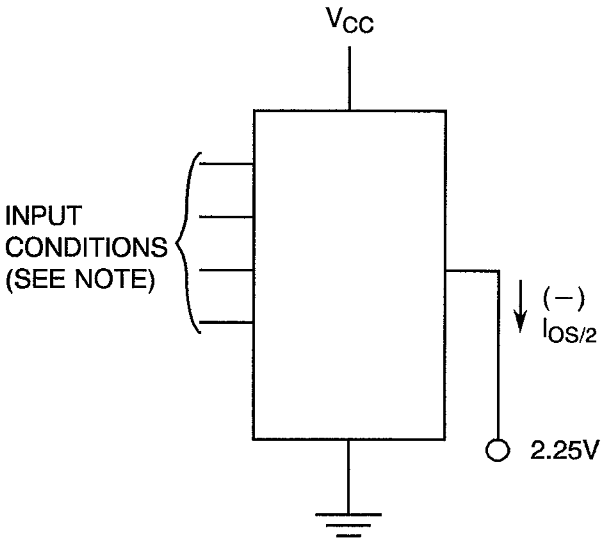
FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(e) - HIGH LEVEL OUTPUT VOLTAGE



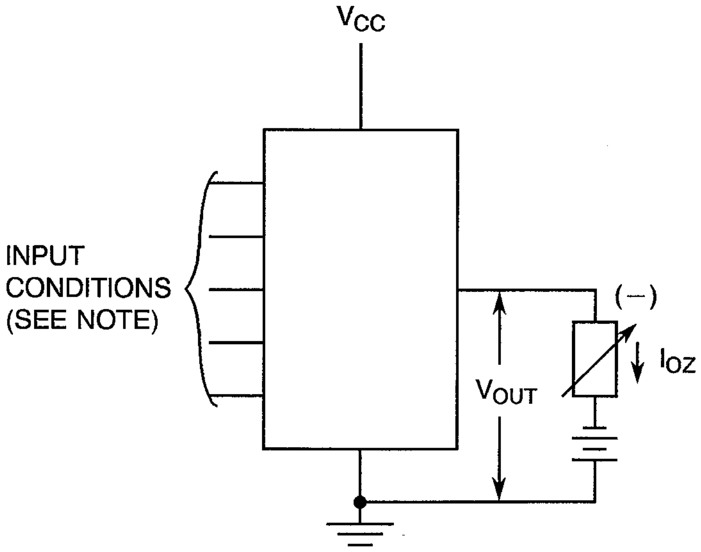
NOTES
1. Test per Truth Table.

FIGURE 4(f) - ONE HALF SHORT CIRCUIT OUTPUT CURRENT



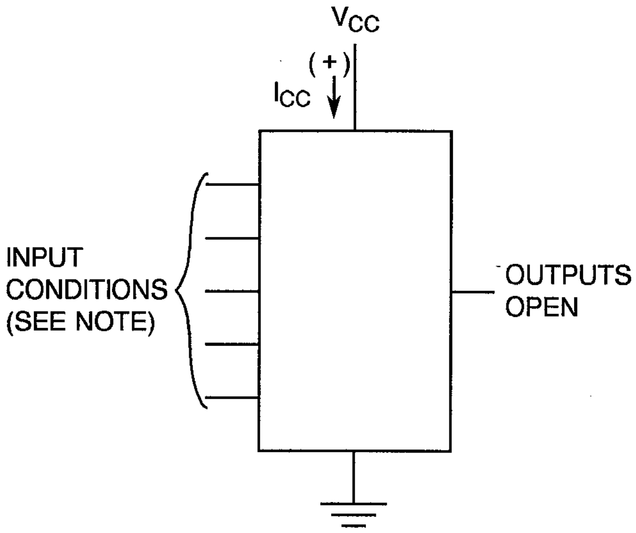
NOTES
1. Test per Truth Table.
2. Each output to be tested separately.

FIGURE 4(g) - OFF STATE OUTPUT CURRENT



NOTES
1. Output Control ($\bar{G}$) at V_{IH} min.

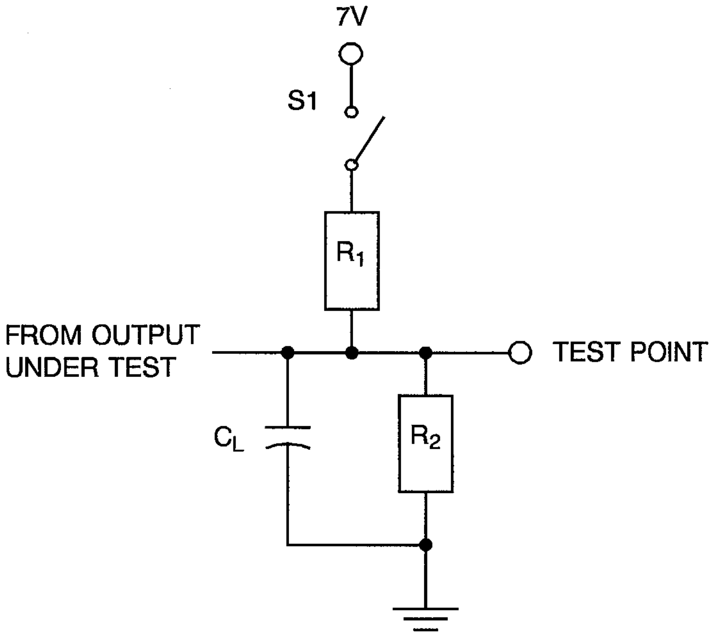
FIGURE 4(h) - SUPPLY CURRENT



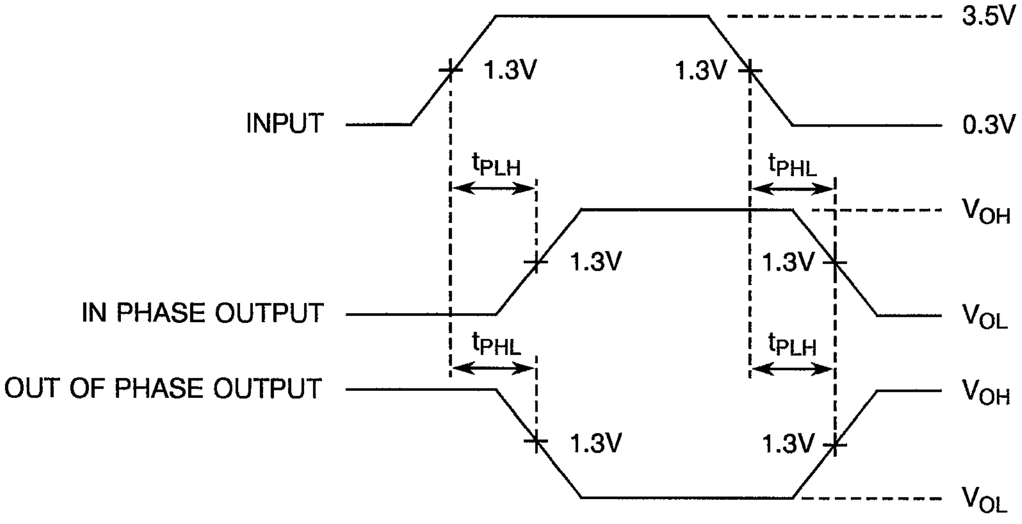
NOTES
1. See Note 4 on Page 20.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(i) - DYNAMIC TEST AND SWITCHING WAVEFORMS



VOLTAGE WAVEFORMS - PROPAGATION DELAY TIMES

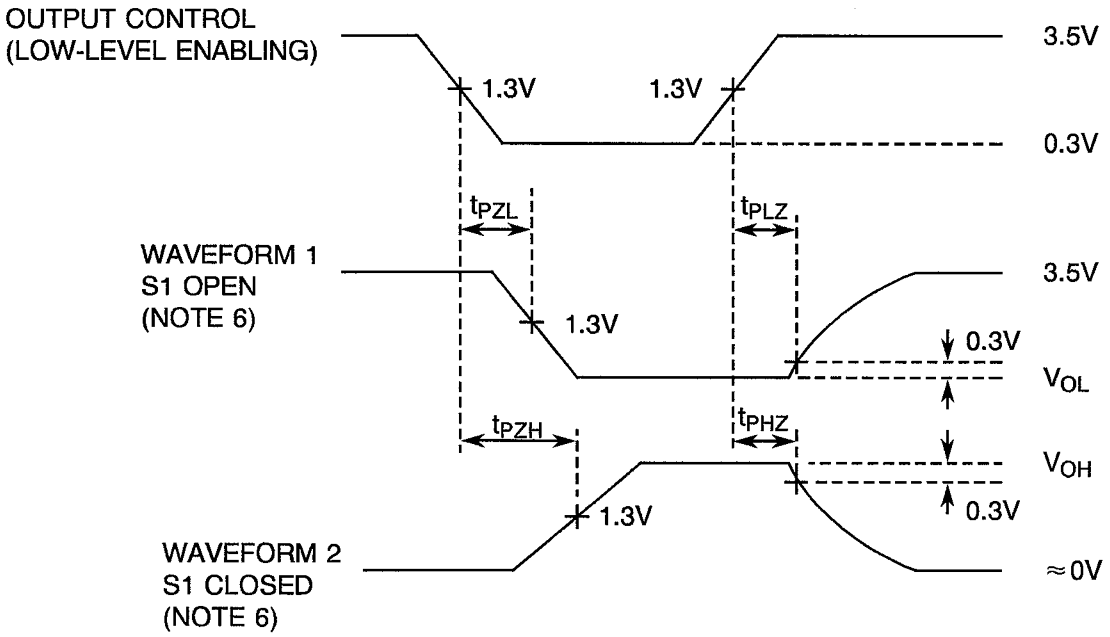


NOTES: See Note 5 on Page 26.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(i) - DYNAMIC TEST AND SWITCHING WAVEFORMS (CONTINUED)

VOLTAGE WAVEFORMS - ENABLE AND DISABLE TIMES



NOTES

1. The generator has the following characteristics: $t_r = t_f = 2ns$, PRR = 1MHz, $Z_{out} = 50\Omega$, Duty Cycle = 50%.
2. $C_L = 50pF$ ±5% including scope probe, wiring and stray capacitance without package in test fixture.
3. Each output tested separately.
4. $R_1 = R_2 = 500\Omega$ ±5%.
5. For measurement of Propagation Times, Switch S1 is open.
6. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the Output Control.

   Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the Output Control.

TABLE 4 - PARAMETER DRIFT VALUES

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2 to 13	Input Current High Level 1	I_{IH1}	As per Table 2	As per Table 2	±20 or (1) ±0.5	% µA
38 to 49	Input Current Low Level	I_{IL}	As per Table 2	As per Table 2	±10	µA
50 to 51	Output Voltage Low Level	V_{OL}	As per Table 2	As per Table 2	±60	mV
52 to 53	Output Voltage High Level 1	V_{OH1}	As per Table 2	As per Table 2	±200	mV
54 to 55	Output Voltage High Level 2	V_{OH2}	As per Table 2	As per Table 2	±200	mV
56 to 57	Output Voltage High Level 3	V_{OH3}	As per Table 2	As per Table 2	±200	mV

NOTES

1. Whichever is greater referred to the initial value.

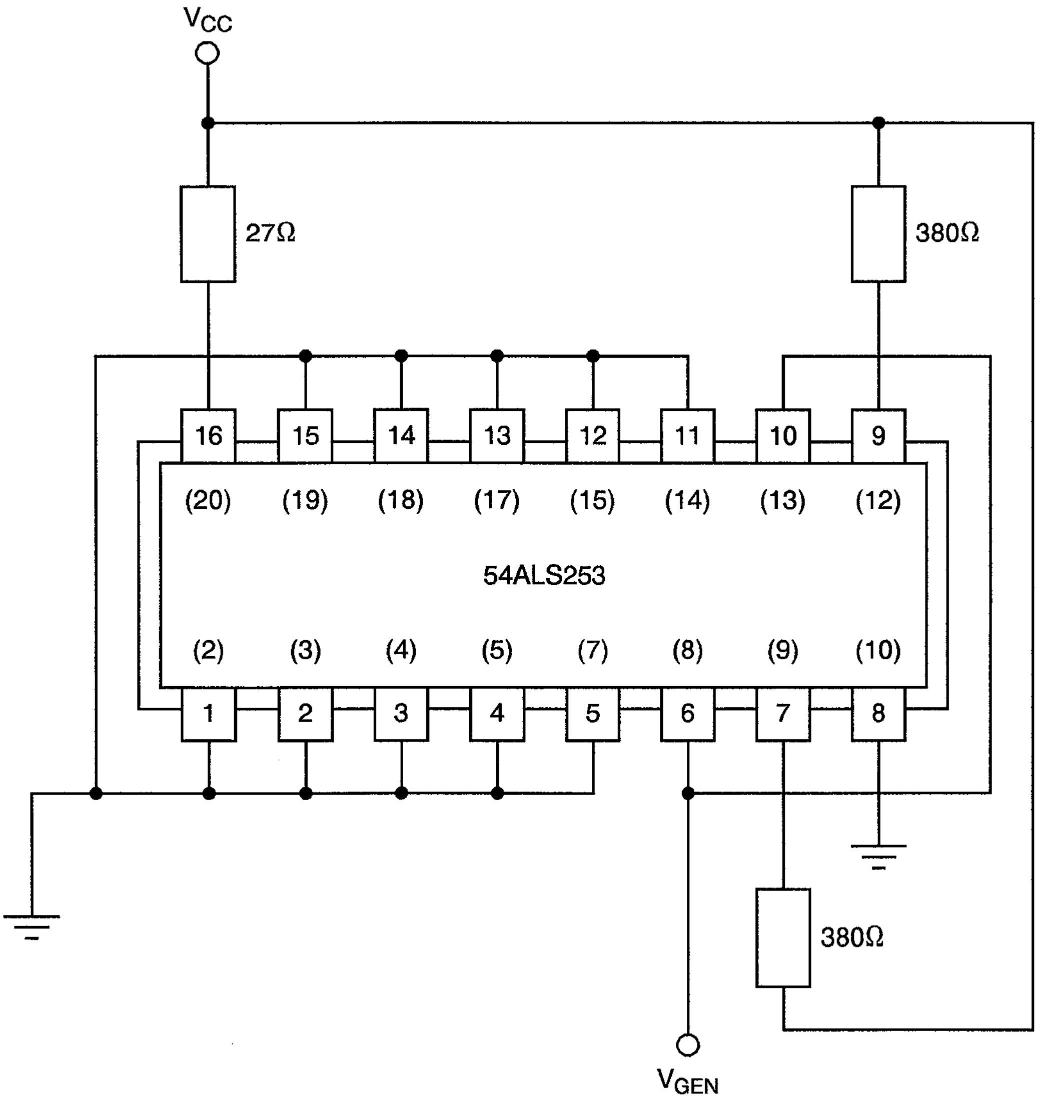
TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

NO.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T_{amb}	+125(+0−5)	°C
2	Power Supply Voltage	V_{CC}	+5(+0.5−0)	V
3	Pulse Voltage	V_{GEN}	0.5 max. to 3.0 min.	Vac
4	Frequency	f	100 (See Note 1)	Hz
5	Fan-out	-	10	-
6	Rise Time	t_r	50 max.	µs
7	Fall Time	t_f	50 max.	µs
8	Duty Cycle	-	20 min.	%

NOTES

1. Tolerance ±10%.

FIGURE 5 - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST



NOTES

1. Pin numbers in parenthesis are for the chip carrier package.

4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 9000)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.4 Conditions for Operating Life Tests

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 Electrical Circuits for Operating Life Tests

Circuits for use in performing the operating life tests are shown in Figure 5.

4.8.6 Conditions for High Temperature Storage Test

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be $T_{amb} = +150(+0\text{-}5)$ °C.

TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTS

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS		UNIT
					(Δ)	ABSOLUTE	
2 to 13	Input Current High Level 1	I_{IH1}	As per Table 2	As per Table 2	±1	-	µA
14 to 25	Input Current High Level 2 (Max. Input Voltage)	I_{IH2}	As per Table 2	As per Table 2	-	100	µA
38 to 49	Input Current Low Level	I_{IL}	As per Table 2	As per Table 2	±10	-	µA
50 to 51	Output Voltage Low Level	V_{OL}	As per Table 2	As per Table 2	±60	-	mV
52 to 53	Output Voltage High Level 1	V_{OH1}	As per Table 2	As per Table 2	±200	-	mV
54 to 55	Output Voltage High Level 2	V_{OH2}	As per Table 2	As per Table 2	±200	-	mV
56 to 57	Output Voltage High Level 3	V_{OH3}	As per Table 2	As per Table 2	±200	-	mV
64	Supply Current Outputs Enabled	I_{CC}	As per Table 2	As per Table 2	±20	-	%
65	Supply Current Outputs Disabled	I_{CCZ}	As per Table 2	As per Table 2	±20	-	%

APPENDIX 'A'

AGREED DEVIATIONS FOR TEXAS INSTRUMENTS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 4.2.1	Scanning Electron Microscope (SEM) Inspection may be performed using TIF document TIF 3.61.610.001.
Para. 4.2.2	Prior to Die Shear Test TIF may perform a Radiographic Inspection on the randomly chosen samples to be subjected to this test, using TIF document TI 50.42-3002.
Para. 4.2.3	Radiographic Inspection may be performed using TIF document TI 50.42-3002.